



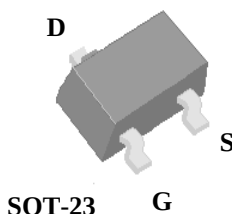
**Advanced Power
Electronics Corp.**

AP2315GEN

RoHS-compliant Product

*P-CHANNEL ENHANCEMENT MODE
POWER MOSFET*

- ▼ Simple Drive Requirement
- ▼ Small Package Outline
- ▼ Surface Mount Device

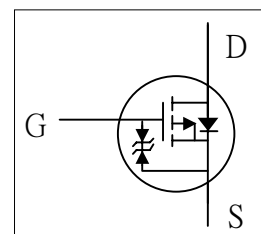


BV_{DSS}	-30V
$R_{DS(ON)}$	$1.25\ \Omega$
I_D	- 840mA

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The SOT-23 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	± 16	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current ³	-840	mA
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current ³	-670	mA
I_{DM}	Pulsed Drain Current ¹	-2.5	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	0.69	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	180	$^\circ\text{C/W}$



AP2315GEN

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =-1mA	-	-0.1	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-0.8A	-	-	1.25	Ω
		V _{GS} =-4.5V, I _D =-0.5A	-	-	2.4	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-0.8A	-	880	-	mS
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =-24V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±16V	-	-	±30	uA
Q _g	Total Gate Charge ²	I _D =-0.8A	-	1	1.6	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-25V	-	0.6	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	0.4	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	10	-	ns
t _r	Rise Time	I _D =-0.8A	-	8	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-10V	-	22	-	ns
t _f	Fall Time	R _D =18.8Ω	-	17	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	30	50	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	15	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	10	-	pF

Source-Drain Diode

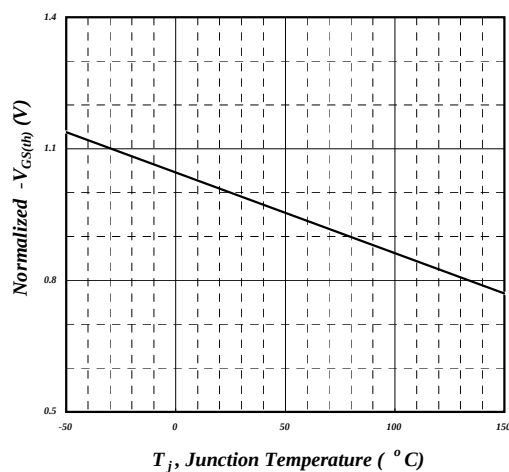
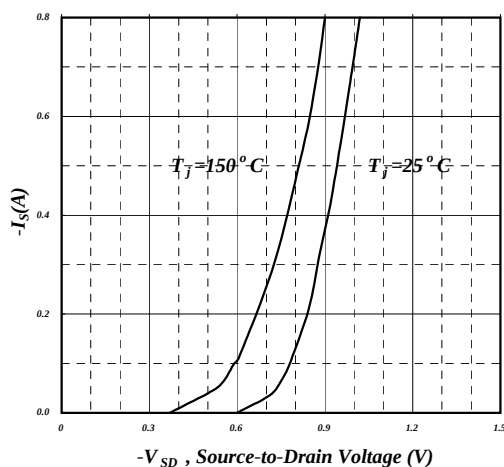
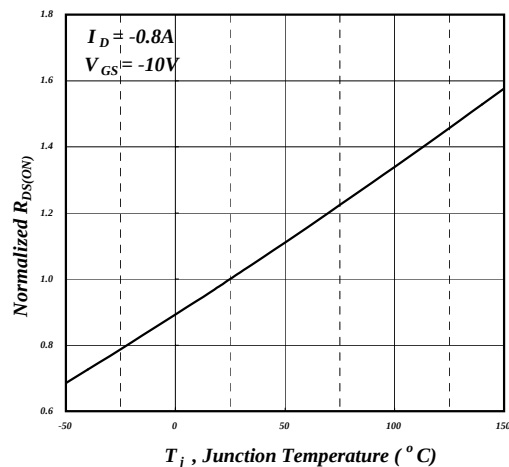
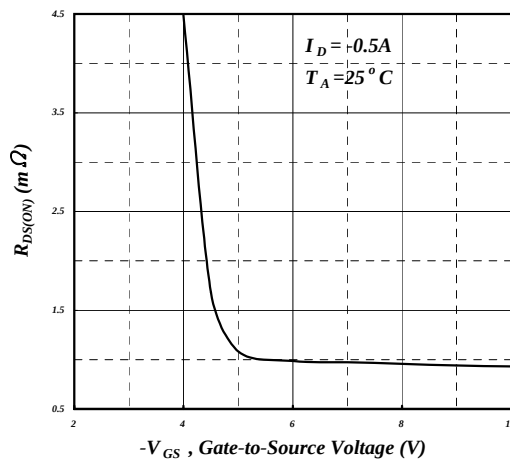
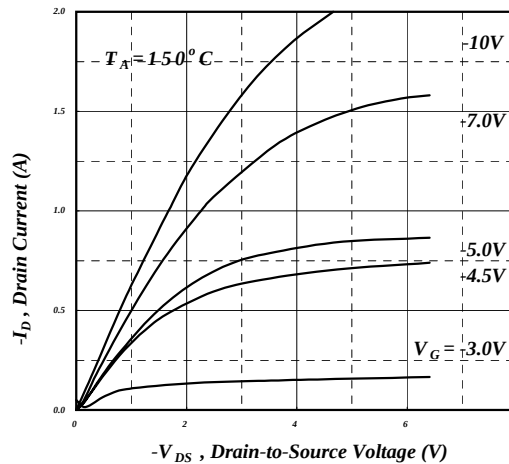
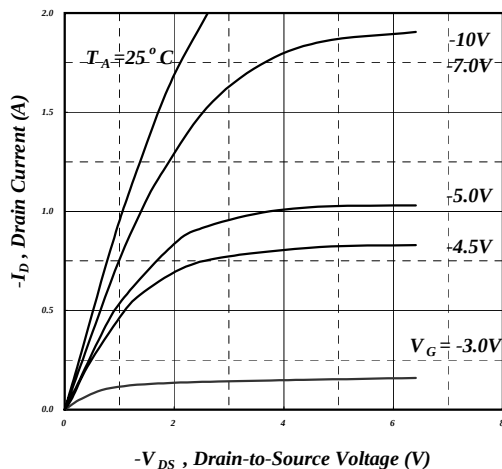
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.1A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time	I _S =-0.8A, V _{GS} =0V,	-	27	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	30	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board ;400°C/W when mounted on min. copper pad.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.



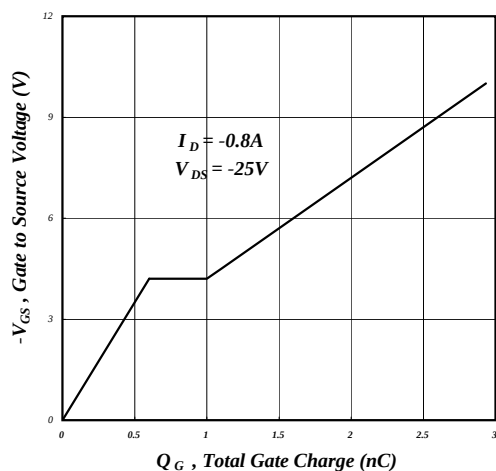


Fig 7. Gate Charge Characteristics

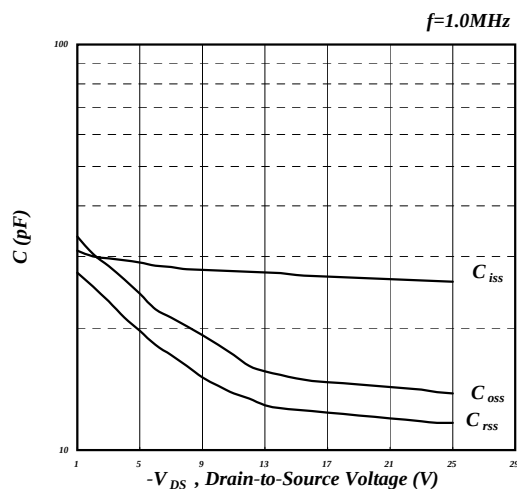


Fig 8. Typical Capacitance Characteristics

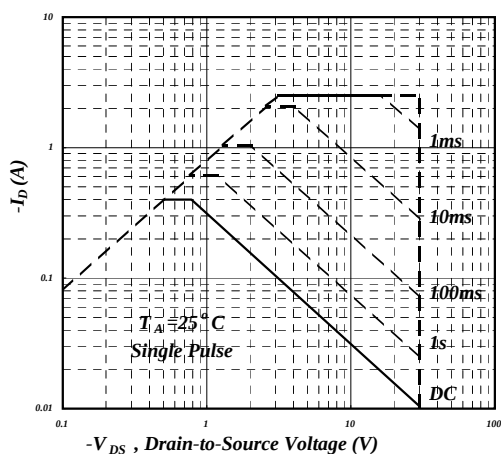


Fig 9. Maximum Safe Operating Area

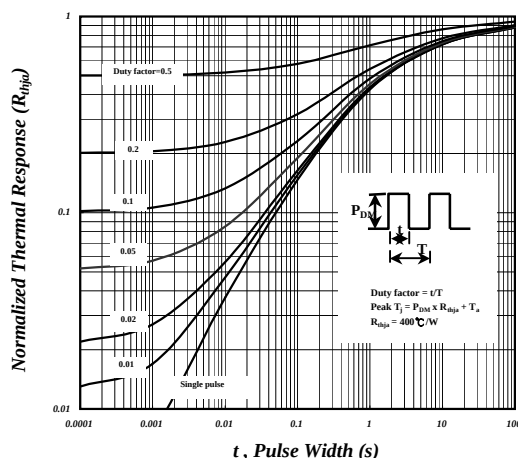


Fig 10. Effective Transient Thermal Impedance

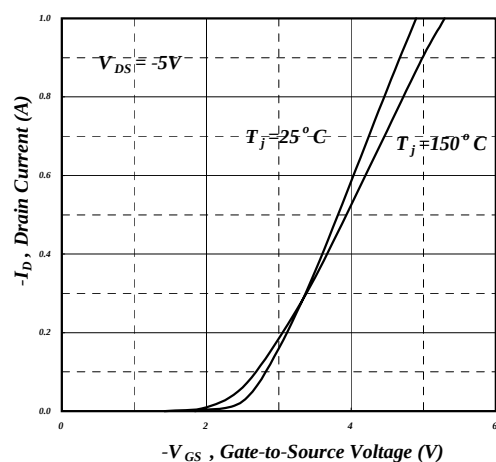


Fig 11. Transfer Characteristics

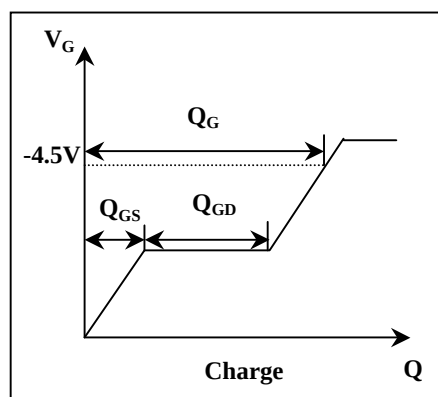
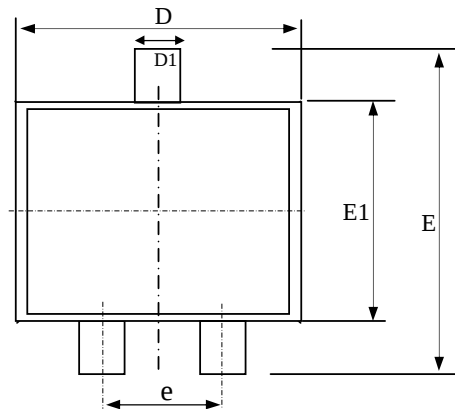


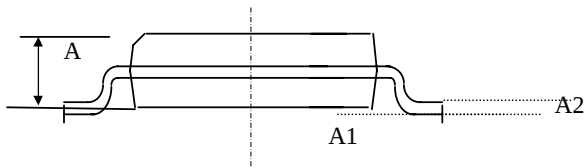
Fig 12. Gate Charge Waveform



Package Outline : SOT-23



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.00	1.15	1.30
A1	0.00	--	0.10
A2	0.10	0.15	0.25
D1	0.30	0.40	0.50
e	1.70	2.00	2.30
D	2.70	2.90	3.10
E	2.40	2.65	3.00
E1	1.40	1.50	1.60



- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : SOT-23

